



TPC8021-H(TE12LQ,M Information



For Reference Only

Part Number TPC8021-H(TE12LQ,M

ManufacturerToshiba Semiconductor and StorageCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 11A SOP8 2-6J1B

Package 8-SOIC (0.173", 4.40mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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TPC8021-H(TE12LQ,M Specifications

Manufacturer Part Number TPC8021-H(TE12LQ,M Manufacturer Toshiba Semiconductor and Storage Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.173", 4.40mm Width) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ ImA Gate Charge (Qg) (Max) @ Vgs 11nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 640pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1W (Ta) Rds On (Max) @ Id, Vgs 17 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOP (5.5x6.0) Package / Case 8-SOIC (0.173", 4.40mm Width)		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single 8-SOIC (0.173", 4.40mm Width) Series - FET Type N-Channel Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Inuc Capacitance (Ciss) (Max) @ Vds Vgs (Max) ### 20V ### 20	Manufacturer Part Number	TPC8021-H(TE12LQ,M
Package 8-SOIC (0.173", 4.40mm Width) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ ImA Gate Charge (Qg) (Max) @ Vgs 11nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 640pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1W (Ta) Rds On (Max) @ Id, Vgs 17 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOP (5.5x6.0) Package / Case 8-SOIC (0.173", 4.40mm Width)	Manufacturer	Toshiba Semiconductor and Storage
Package 8-SOIC (0.173", 4.40mm Width) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ 1mA Gate Charge (Qg) (Max) @ Vgs 11nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 640pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1W (Ta) Rds On (Max) @ Id, Vgs 17 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOP (5.5x6.0) Package / Case 8-SOIC (0.173", 4.40mm Width)	Category	Discrete Semiconductor Products
Series - N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ 1mA Gate Charge (Qg) (Max) @ Vgs 11nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 640pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1W (Ta) Rds On (Max) @ Id, Vgs 17 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOP (5.5x6.0) Package / Case 8-SOIC (0.173", 4.40mm Width)		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ 1mA Gate Charge (Qg) (Max) @ Vgs 11nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 640pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1W (Ta) Rds On (Max) @ Id, Vgs 17 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOP (5.5x6.0) Package / Case 8-SOIC (0.173", 4.40mm Width)	Package	8-SOIC (0.173", 4.40mm Width)
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 11nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 17 mOhm @ 5.5A, 10V Operating Temperature Surface Mount Supplier Device Package Package / Case MOSFET (Metal Oxide) 30V MOSFET (Metal Oxide) 30V 11A (Ta) 4.5V, 10V 2.3V @ 1mA 6.40pF @ 10V 4.5V, 10V 6.40pF @ 10V 4.5V 6.40pF @ 10V 6.40p	Series	-
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 11nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 17 mOhm @ 5.5A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case 30V 11A (Ta) 4.5V, 10V 2.3V @ 1mA 4.5V, 10V 640pF @ 10V 4.5V 4.	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 11A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ 1mA Gate Charge (Qg) (Max) @ Vgs 11nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 640pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1W (Ta) Rds On (Max) @ Id, Vgs 17 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOP (5.5x6.0) Package / Case 8-SOIC (0.173", 4.40mm Width)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Ith (Ta) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.173", 4.40mm Width)	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 640pF @ 10V Vgs (Max) +20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 17 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.173", 4.40mm Width)	Current - Continuous Drain (Id) @ 25°C	11A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 640pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 17 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOP (5.5x6.0) Package / Case 8-SOIC (0.173", 4.40mm Width)	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 17 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOP (5.5x6.0) Package / Case 8-SOIC (0.173", 4.40mm Width)	Vgs(th) (Max) @ Id	2.3V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1W (Ta)Rds On (Max) @ Id, Vgs17 mOhm @ 5.5A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOP (5.5x6.0)Package / Case8-SOIC (0.173", 4.40mm Width)	Gate Charge (Qg) (Max) @ Vgs	11nC @ 10V
FET Feature - Power Dissipation (Max) 1W (Ta) Rds On (Max) @ Id, Vgs 17 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOP (5.5x6.0) Package / Case 8-SOIC (0.173", 4.40mm Width)	Input Capacitance (Ciss) (Max) @ Vds	640pF @ 10V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 17 mOhm @ 5.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOP (5.5x6.0) Package / Case 8-SOIC (0.173", 4.40mm Width)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs17 mOhm @ 5.5A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOP (5.5x6.0)Package / Case8-SOIC (0.173", 4.40mm Width)	FET Feature	-
Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOP (5.5x6.0) Package / Case 8-SOIC (0.173", 4.40mm Width)	Power Dissipation (Max)	1W (Ta)
Mounting Type Surface Mount Supplier Device Package 8-SOP (5.5x6.0) Package / Case 8-SOIC (0.173", 4.40mm Width)	Rds On (Max) @ Id, Vgs	17 mOhm @ 5.5A, 10V
Supplier Device Package 8-SOP (5.5x6.0) Package / Case 8-SOIC (0.173", 4.40mm Width)	Operating Temperature	150°C (TJ)
Package / Case 8-SOIC (0.173", 4.40mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SOP (5.5x6.0)
Report errors?	Package / Case	8-SOIC (0.173", 4.40mm Width)
		Report errors?

TPC8021-H(TE12LQ,M Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

TPC8021-H(TE12LQ,M Payment Methods



















TPC8021-H(TE12LQ,M Shipping Methods













If you have any question about TPC8021-H(TE12LQ,M, please do not hesitate to contact us!

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